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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M7
Core Size	32-Bit Single-Core
Speed	216MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, MMC/SD/SDIO, QSPI, SAI, SPDIF, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	140
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f765igt6

  - Refreshed by software
- DMA capability to read the final conversion data
- Interrupts: end of conversion, overrun, analog watchdog, short circuit, input serial channel clock absence
- “regular” or “injected” conversions:
  - “regular” conversions can be requested at any time or even in continuous mode without having any impact on the timing of “injected” conversions
  - “injected” conversions for precise timing and with high conversion priority

2.43 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with the temperature. The conversion range is between 1.7 V and 3.6 V. The temperature sensor is internally connected to the same input channel as V_{BAT}, ADC1_IN18, which is used to convert the sensor output voltage into a digital value. When the temperature sensor and V_{BAT} conversion are enabled at the same time, only V_{BAT} conversion is performed.

As the offset of the temperature sensor varies from chip to chip due to process variation, the internal temperature sensor is mainly suitable for applications that detect temperature changes instead of absolute temperatures. If an accurate temperature reading is needed, then an external temperature sensor part should be used.

Table 10. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)

Pin Number										Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32F765xx STM32F767xx						STM32F768Ax STM32F769xx									
LQFP100	LQFP144	UFBGA176	LQFP176	LQFP208	TFBGA216	WLCSP180[1]	LQFP176	LQFP208	TFBGA216						
81	114	B12	142	164	B12	A4	142	164	B12	PD0	I/O	FT	-	DFSDM1_CKIN6, DFSDM1_DATIN7, UART4_RX, CAN1_RX, FMC_D2, EVENTOUT	-
82	115	C12	143	165	C12	D5	143	165	C12	PD1	I/O	FT	-	DFSDM1_DATIN6, DFSDM1_CKIN7, UART4_TX, CAN1_TX, FMC_D3, EVENTOUT	--
83	116	D12	144	166	D12	D6	144	166	D12	PD2	I/O	FT	-	TRACED2, TIM3_ETR, UART5_RX, SDMMC1_CMD, DCMI_D11, EVENTOUT	-
84	117	D11	145	167	C11	B5	145	167	C11	PD3	I/O	FT	-	DFSDM1_CKOUT, SPI2_SCK/I2S2_CK, DFSDM1_DATIN0, USART2_CTS, FMC_CLK, DCMI_D5, LCD_G7, EVENTOUT	-
85	118	D10	146	168	D11	A5	146	168	D11	PD4	I/O	FT	-	DFSDM1_CKIN0, USART2_RTS, FMC_NOE, EVENTOUT	-
86	119	C11	147	169	C10	C5	147	169	C10	PD5	I/O	FT	-	USART2_TX, FMC_NWE, EVENTOUT	-
-	120	D8	148	170	F8	B6	148	170	F8	VSS	S	-	-	-	-
-	121	C8	149	171	E9	A6	149	171	E9	VDDSDMMC	S	-	-	-	-
87	122	B11	150	172	B11	E6	150	172	B11	PD6	I/O	FT	-	DFSDM1_CKIN4, SPI3_MOSI/I2S3_SD, SAI1_SD_A, USART2_RX, DFSDM1_DATIN1, SDMMC2_CK, FMC_NWAIT, DCMI_D10, LCD_B2, EVENTOUT	-

Table 12. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	I2C4/UART5/TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1/DFSDM1/CEC	I2C1/2/3/4/USART1/CEC	SPI1/I2S1/SPI2/I2S2/SPI3/I2S3/SPI4/5/6	SPI2/I2S2/SPI3/I2S3/SAI1/I2C4/UART4/DFSDM1	SPI2/I2S2/SPI3/I2S3/SPI6/USART1/2/3/UART5/DFSDM1/SPDIF	SPI6/SAI2/USART6/UART4/5/7/8/OTG_FS/SPDIF	CAN1/2/TIM12/13/14/QUADSPI/FMC/LCD	SAI2/QUADSPI/SDMMC2/DFSDM1/OTG2_HS/OTG1_FS/LCD	I2C4/CAN3/SDMMC2/ETH	UART7/FMC/SDMMC1/MDIOS/OTG2_FS	DCMI/LCD/DSI	LCD	SYS
Port H	PH14	-	-	-	TIM8_CH2N	-	-	-	-	UART4_RX	CAN1_RX	-	-	FMC_D22	DCMI_D4	LCD_G3	EVENTOUT
	PH15	-	-	-	TIM8_CH3N	-	-	-	-	-	-	-	-	FMC_D23	DCMI_D11	LCD_G4	EVENTOUT
Port I	PI0	-	-	TIM5_CH4	-	-	SPI2_NSS/I2S2_WS	-	-	-	-	-	-	FMC_D24	DCMI_D13	LCD_G5	EVENTOUT
	PI1	-	-	-	TIM8_BKIN2	-	SPI2_SCK/I2S2_CK	-	-	-	-	-	-	FMC_D25	DCMI_D8	LCD_G6	EVENTOUT
	PI2	-	-	-	TIM8_CH4	-	SPI2_MISO	-	-	-	-	-	-	FMC_D26	DCMI_D9	LCD_G7	EVENTOUT
	PI3	-	-	-	TIM8_ETR	-	SPI2_MOSI/I2S2_SD	-	-	-	-	-	-	FMC_D27	DCMI_D10	-	EVENTOUT
	PI4	-	-	-	TIM8_BKIN	-	-	-	-	-	-	SAI2_MCK_A	-	FMC_NBL2	DCMI_D5	LCD_B4	EVENTOUT
	PI5	-	-	-	TIM8_CH1	-	-	-	-	-	-	SAI2_SCK_A	-	FMC_NBL3	DCMI_VSYNC	LCD_B5	EVENTOUT
	PI6	-	-	-	TIM8_CH2	-	-	-	-	-	-	SAI2_SD_A	-	FMC_D28	DCMI_D6	LCD_B6	EVENTOUT
	PI7	-	-	-	TIM8_CH3	-	-	-	-	-	-	SAI2_FS_A	-	FMC_D29	DCMI_D7	LCD_B7	EVENTOUT
	PI8	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PI9	-	-	-	-	-	-	-	-	UART4_RX	CAN1_RX	-	-	FMC_D30	-	LCD_VSYNC	EVENTOUT
	PI10	-	-	-	-	-	-	-	-	-	-	-	ETH_MII_RX_ER	FMC_D31	-	LCD_HSYNC	EVENTOUT
	PI11	-	-	-	-	-	-	-	-	-	LCD_G6	OTG_HS_ULPI_DIR	-	-	-	-	EVENTOUT

7. The over-drive mode is not supported when the internal regulator is OFF.
8. To sustain a voltage higher than VDD+0.3, the internal Pull-up and Pull-Down resistors must be disabled
9. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax}.
10. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax}.

Table 18. Limitations depending on the operating power supply range

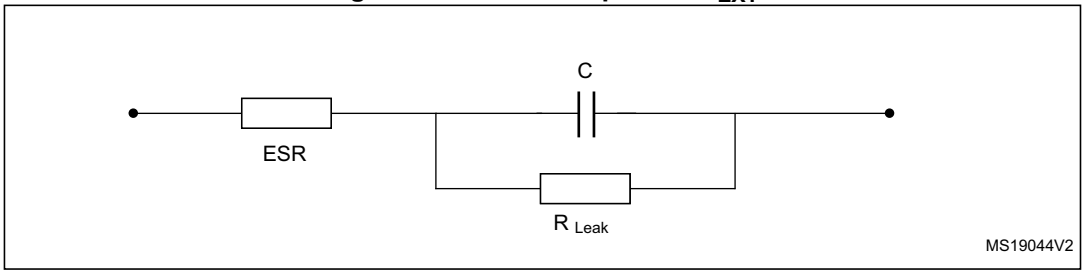
Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait states ($f_{Flashmax}$)	Maximum HCLK frequency vs Flash memory wait states (1)(2)	I/O operation	Possible Flash memory operations
V_{DD} =1.7 to 2.1 V(3)	Conversion time up to 1.2 Msps	20 MHz	180 MHz with 8 wait states and over-drive OFF	No I/O compensation	8-bit erase and program operations only
V_{DD} = 2.1 to 2.4 V	Conversion time up to 1.2 Msps	22 MHz	216 MHz with 9 wait states and over-drive ON	No I/O compensation	16-bit erase and program operations
V_{DD} = 2.4 to 2.7 V	Conversion time up to 2.4 Msps	24 MHz	216 MHz with 8 wait states and over-drive ON	I/O compensation works	16-bit erase and program operations
V_{DD} = 2.7 to 3.6 V(4)	Conversion time up to 2.4 Msps	30 MHz	216 MHz with 6 wait states and over-drive ON	I/O compensation works	32-bit erase and program operations

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.
2. Thanks to the ART accelerator on ITCM interface and L1-cache on AXI interface, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator or L1-cache allows to achieve a performance equivalent to 0-wait state program execution.
3. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to *Section 2.18.2: Internal reset OFF*).
4. The voltage range for USB full speed PHYs can drop down to 2.7 V. However the electrical characteristics of D- and D+ pins will be degraded between 2.7 and 3 V.

5.3.2 VCAP1/VCAP2 external capacitor

Stabilization for the main regulator is achieved by connecting an external capacitor C_{EXT} to the VCAP1/VCAP2 pins. C_{EXT} is specified in *Table 19*.

Figure 27. External capacitor C_{EXT}



1. Legend: ESR is the equivalent series resistance.

1. Guaranteed by characterization results.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 33. Typical and maximum current consumption in Sleep mode, regulator ON

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in Sleep mode	All peripherals enabled(2)	216	128	144(3)	190(3)	-	mA
			200	119	134	180	214	
			180	105	118(3)	153(3)	178(3)	
			168	93	105	136	156	
			144	72	80	107	124	
			60	33	39	65	82	
			25	17	21	47	65	
		All peripherals disabled	216	18	25(3)	71(3)	-	
			200	17	24	70	112	
			180	14	20(3)	54(3)	75(3)	
			168	13	18	49	69	
			144	10	14	40	58	
			60	6	10	36	53	
			25	4	8	34	51	

1. Guaranteed by characterization results, unless otherwise specified.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. Guaranteed by test in production.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid a current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see *Table 39: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT}$

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

Table 38. Switching output I/O current consumption(1)

Symbol	Parameter	Conditions	I/O toggling frequency (fsw) MHz	Typ V_{DD} = 3.3 V	Typ V_{DD} = 1.8 V	Unit
I_{DDIO}	I/O switching Current	C_{EXT} = 0 pF $C = C_{INT} + C_S + C_{EXT}$	2	0.1	0.1	mA
			8	0.4	0.2	
			25	1.1	0.7	
			50	2.4	1.3	
			60	3.1	1.6	
			84	4.3	2.4	
			90	4.9	2.6	
			100	5.4	2.8	
		C_{EXT} = 10 pF $C = C_{INT} + C_S + C_{EXT}$	2	0.2	0.1	
			8	0.6	0.3	
			25	1.8	1.1	
			50	3.1	2.3	
			60	4.6	3.4	
			84	9.7	3.6	
			90	10.12	5.2	
			100	14.92	5.4	

5.3.8 Wakeup time from low-power modes

The wakeup times given in *Table 40* are measured starting from the wakeup event trigger up to the first instruction executed by the CPU:

- For Stop or Sleep modes: the wakeup event is WFE.
- WKUP (PA0) pin is used to wakeup from Standby, Stop and Sleep modes.

All timings are derived from tests performed under ambient temperature and V_{DD}=3.3 V.

Table 40. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Typ(1)	Max(1)	Unit
$t_{WUSLEEP}$(2)	Wakeup from Sleep	-	13	13	CPU clock cycles
t_{WUSTOP}(2)	Wakeup from Stop mode with MR/LP regulator in normal mode	Main regulator is ON	14	14.9	µs
		Main regulator is ON and Flash memory in Deep power down mode	104.1	107.6	
		Low power regulator is ON	21.4	24.2	
		Low power regulator is ON and Flash memory in Deep power down mode	111.5	116.5	
t_{WUSTOP}(2)	Wakeup from Stop mode with MR/LP regulator in Under-drive mode	Main regulator in under-drive mode (Flash memory in Deep power-down mode)	107.4	113.2	
		Low power regulator in under-drive mode (Flash memory in Deep power-down mode)	112.7	120	
tWUSTDBY (2)	Wakeup from Standby mode	Exit Standby mode on rising edge	308	313	
		Exit Standby mode on falling edge	307	313	

1. Guaranteed by characterization results.
2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first

Table 56. Flash memory programming (single bank configuration nDBANK=1) (continued)

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
V_{prog}	Programming voltage	32-bit program operation	2.7	-	3	V
		16-bit program operation	2.1	-	3.6	V
		8-bit program operation	1.7	-	3.6	V

1. Guaranteed by characterization results.
2. The maximum programming time is measured after 100K erase operations.

Table 57. Flash memory programming (dual bank configuration nDBANK=0)

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	400	800	ms
		Program/erase parallelism (PSIZE) = x 16	-	250	600	
		Program/erase parallelism (PSIZE) = x 32	-	200	500	
$t_{ERASE64KB}$	Sector (64 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	1100	2400	ms
		Program/erase parallelism (PSIZE) = x 16	-	800	1400	
		Program/erase parallelism (PSIZE) = x 32	-	500	1100	
$t_{ERASE128KB}$	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	2.1	4	s
		Program/erase parallelism (PSIZE) = x 16	-	1.5	2.6	
		Program/erase parallelism (PSIZE) = x 32	-	1	2	
t_{ME}	Mass erase time	Program/erase parallelism (PSIZE) = x 8	-	16	32	s
		Program/erase parallelism (PSIZE) = x 16	-	11	22	
		Program/erase parallelism (PSIZE) = x 32	-	8	16	

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

5.3.17 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 60*. They are based on the EMS levels and classes defined in application note AN1709.

Table 60. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{HCLK} = 216 MHz, conforms to IEC 61000-4-2	2B
V_{FTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, T_A =+25 °C, f_{HCLK} = 168 MHz, conforms to IEC 61000-4-2	5A

As a consequence, it is recommended to add a serial resistor (1 kΩ) located as close as possible to the MCU to the pins exposed to noise (connected to tracks longer than 50 mm on PCB).

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

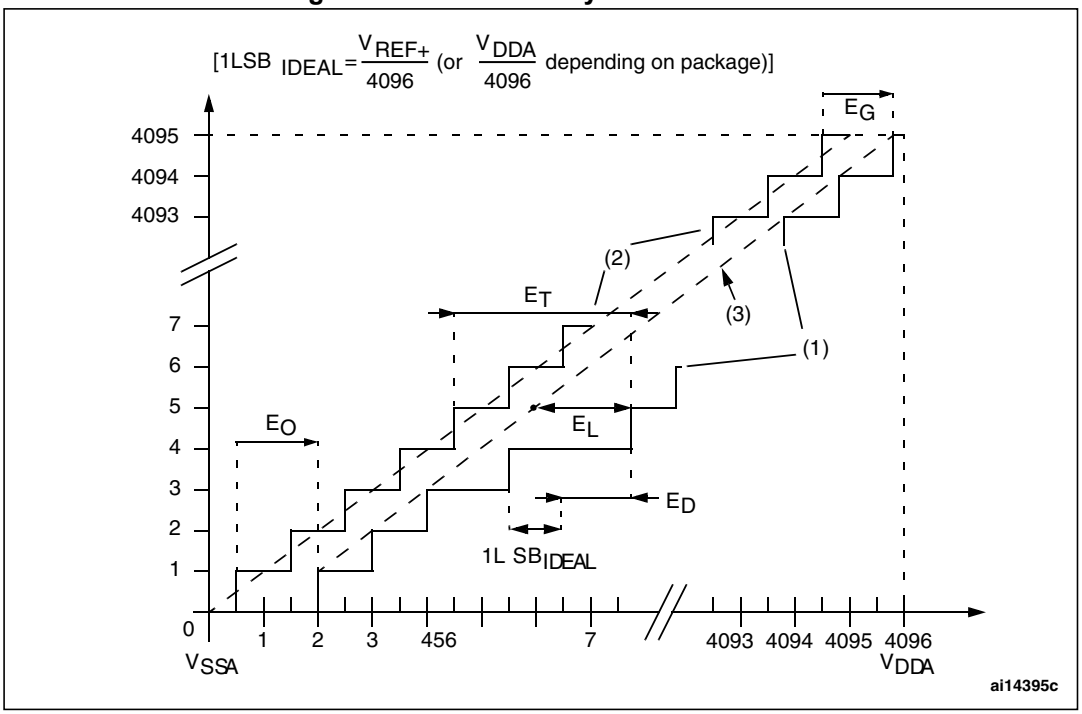
The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Table 71. ADC characteristics (continued)

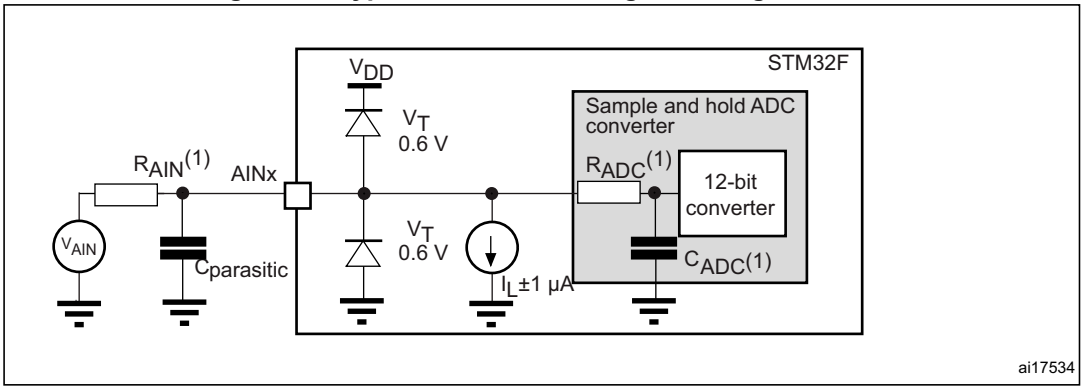
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{TRIG}(2)	External trigger frequency	f_{ADC} = 30 MHz, 12-bit resolution	-	-	1764	kHz
		-	-	-	17	$1/f_{ADC}$
V_{AIN}	Conversion voltage range(3)	-	0 (V_{SSA} or V_{REF-} tied to ground)	-	V_{REF+}	V
R_{AIN}(2)	External input impedance	See *Equation 1* for details	-	-	50	kΩ
R_{ADC}(2)(4)	Sampling switch resistance	-	-	-	6	kΩ
C_{ADC}(2)	Internal sample and hold capacitor	-	-	4	7	pF
t_{lat}(2)	Injection trigger conversion latency	f_{ADC} = 30 MHz	-	-	0.100	µs
			-	-	3(5)	$1/f_{ADC}$
t_{latr}(2)	Regular trigger conversion latency	f_{ADC} = 30 MHz	-	-	0.067	µs
			-	-	2(5)	$1/f_{ADC}$
t_S(2)	Sampling time	f_{ADC} = 30 MHz	0.100	-	16	µs
		-	3	-	480	$1/f_{ADC}$
t_{STAB}(2)	Power-up time	-	-	2	3	µs
t_{CONV}(2)	Total conversion time (including sampling time)	f_{ADC} = 30 MHz 12-bit resolution	0.50	-	16.40	µs
		f_{ADC} = 30 MHz 10-bit resolution	0.43	-	16.34	µs
		f_{ADC} = 30 MHz 8-bit resolution	0.37	-	16.27	µs
		f_{ADC} = 30 MHz 6-bit resolution	0.30	-	16.20	µs
		9 to 492 (t_S for sampling +n-bit resolution for successive approximation)				$1/f_{ADC}$
f_S(2)	Sampling rate (f_{ADC} = 36 MHz, and t_S = 3 ADC cycles)	12-bit resolution Single ADC	-	-	2.4	Msps
		12-bit resolution Interleave Dual ADC mode	-	-	4.5	Msps
		12-bit resolution Interleave Triple ADC mode	-	-	7.2	Msps

Figure 41. ADC accuracy characteristics



1. See also *Table 73*.
2. Example of an actual transfer curve.
3. Ideal transfer curve.
4. End point correlation line.
5. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
   EO = Offset Error: deviation between the first actual transition and the first ideal one.
   EG = Gain Error: deviation between the last ideal transition and the last actual one.
   ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
   EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 42. Typical connection diagram using the ADC



1. Refer to *Table 71* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

Table 80. internal reference voltage (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{Coeff}(2)	Temperature coefficient	-	-	30	50	ppm/°C
t_{START}(2)	Startup time	-	-	6	10	µs

1. Shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design.

Table 81. Internal reference voltage calibration values

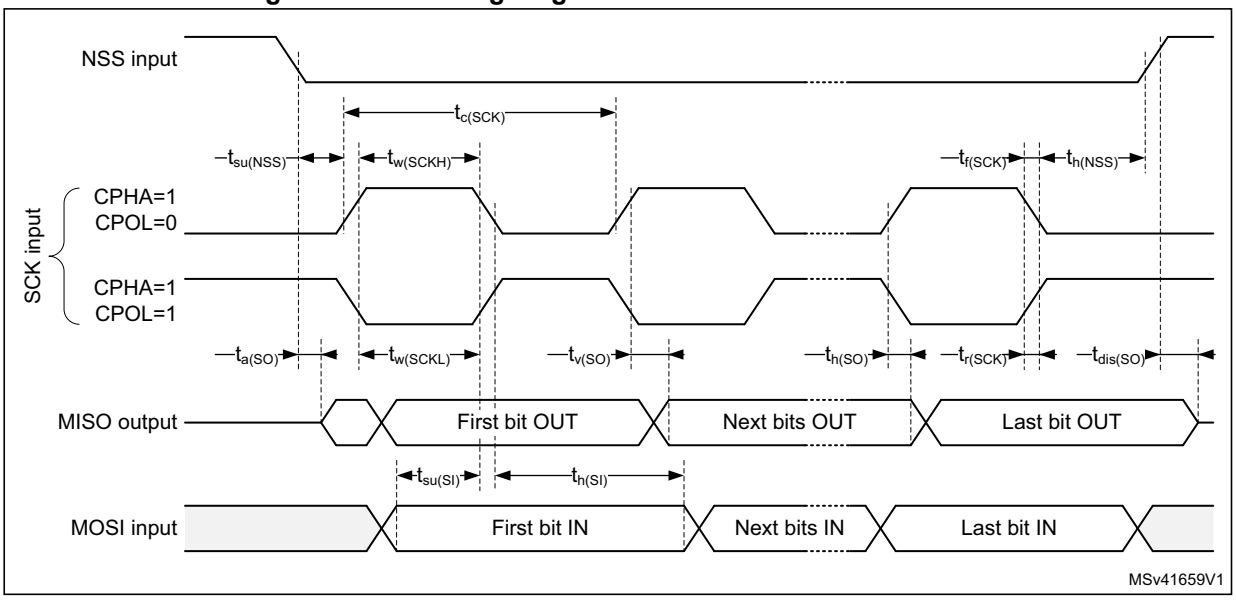
Symbol	Parameter	Memory address
V_{REFIN_CAL}	Raw data acquired at temperature of 30 °C V_{DDA} = 3.3 V	0x1FF0 F44A - 0x1FF0 F44B

5.3.28 DAC electrical characteristics

Table 82. DAC characteristics

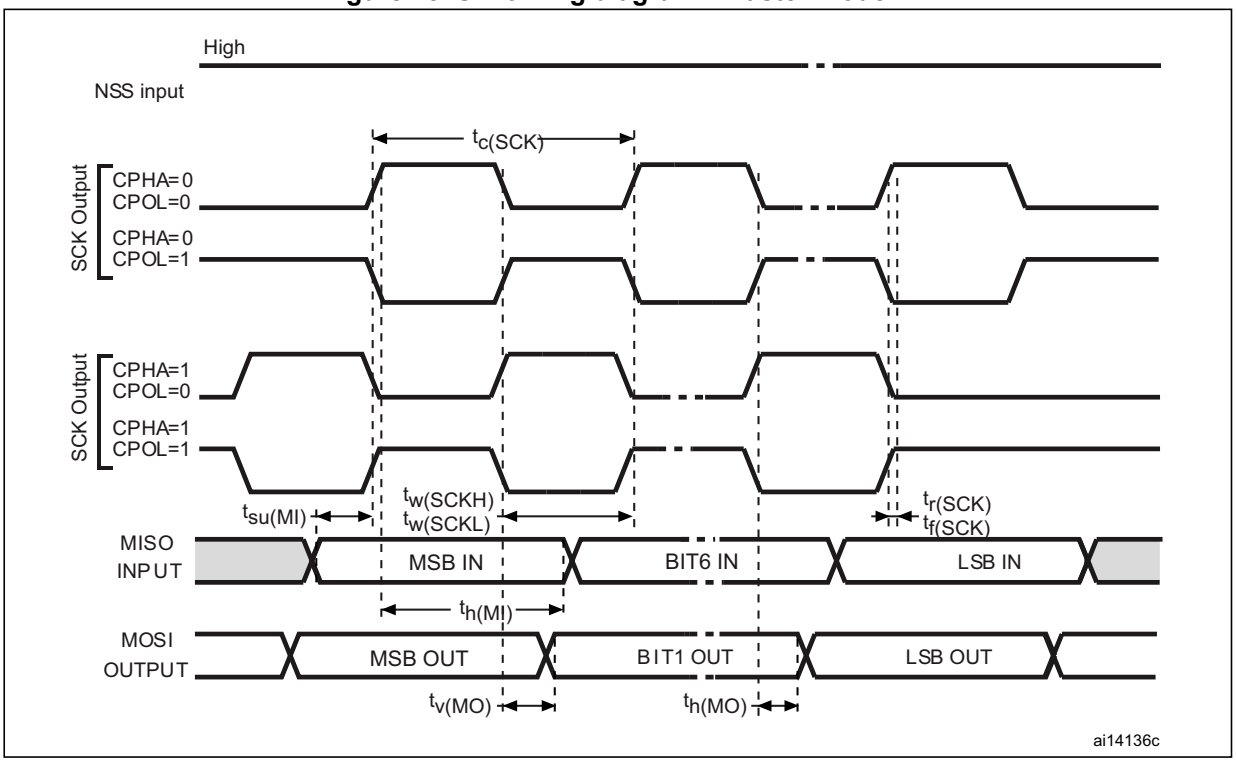
Symbol	Parameter	Min	Typ	Max	Unit	Comments
V_{DDA}	Analog supply voltage	1.7(1)	-	3.6	V	-
V_{REF+}	Reference supply voltage	1.7(1)	-	3.6	V	$V_{REF+} \leq V_{DDA}$
V_{SSA}	Ground	0	-	0	V	-
R_{LOAD}(2)	Resistive load with buffer ON	5	-	-	kΩ	-
R_O(2)	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and V_{SS} to have a 1% accuracy is 1.5 MΩ
C_{LOAD}(2)	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min(2)	Lower DAC_OUT voltage with buffer ON	0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{REF+} = 3.6 V and (0x1C7) to (0xE38) at V_{REF+} = 1.7 V
DAC_OUT max(2)	Higher DAC_OUT voltage with buffer ON	-	-	V_{DDA} – 0.2	V	
DAC_OUT min(2)	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output excursion of the DAC.
DAC_OUT max(2)	Higher DAC_OUT voltage with buffer OFF	-	-	V_{REF+} – 1LSB	V	
I_{VREF+}(4)	DAC DC V_{REF} current consumption in quiescent mode (Standby mode)	-	170	240	µA	With no load, worst code (0x800) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs
		-	50	75		With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs

Figure 47. SPI timing diagram - slave mode and CPHA = 1(1)



1. Measurement points are done at $0.5V_{DD}$ and with external C_L = 30 pF.

Figure 48. SPI timing diagram - master mode(1)



1. Measurement points are done at $0.5V_{DD}$ and with external C_L = 30 pF.

Refer to *Section 5.3.20: I/O port characteristics* for more details on the input/output characteristics.

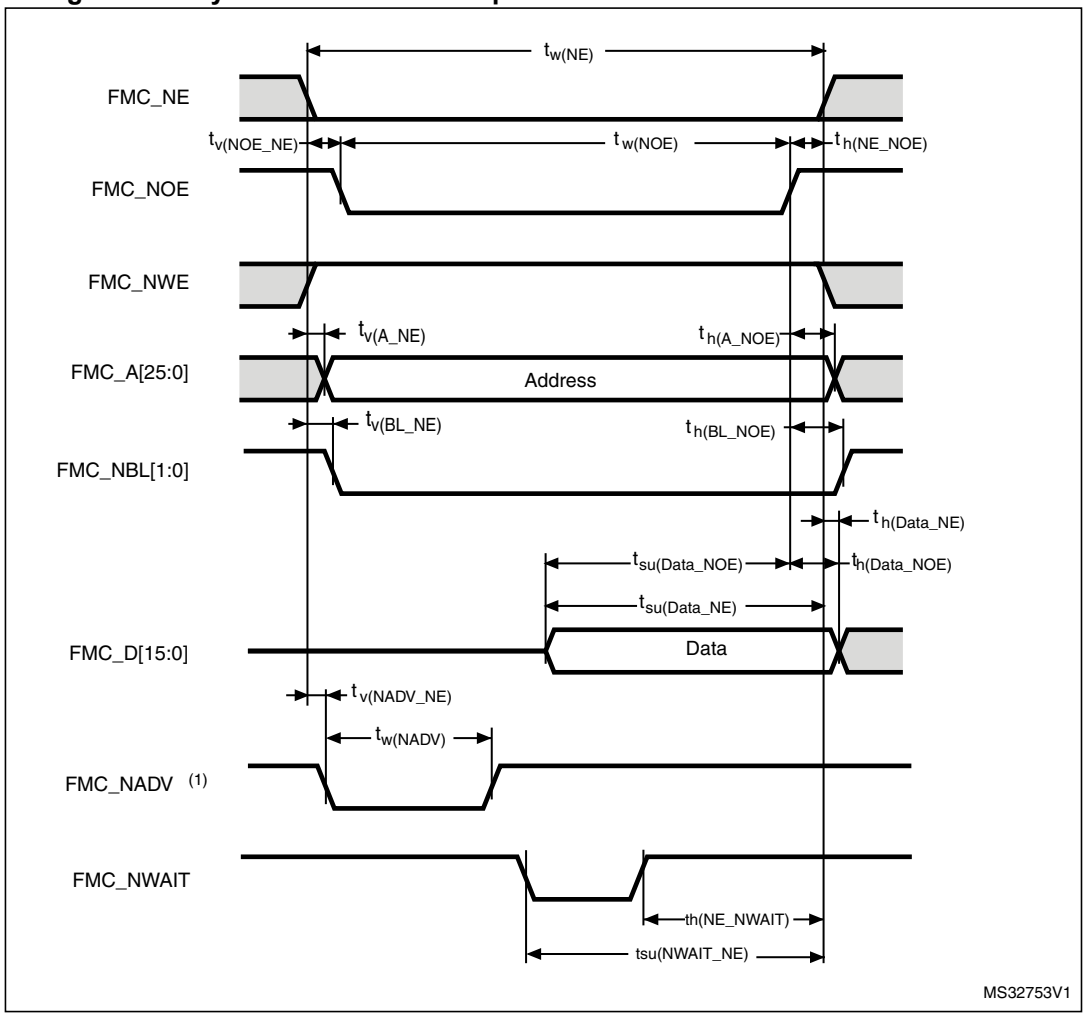
Asynchronous waveforms and timings

Figure 61 through *Figure 64* represent asynchronous waveforms and *Table 100* through *Table 107* provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- AddressSetupTime = 0x1
- AddressHoldTime = 0x1
- DataSetupTime = 0x1 (except for asynchronous NWAIT mode , DataSetupTime = 0x5)
- BusTurnAroundDuration = 0x0
- Capcitive load CL = 30 pF

In all timing tables, the T_{HCLK} is the HCLK clock period

Figure 61. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms



1. Mode 2/B, C and D only. In Mode 1, FMC_NADV is not used.

5.3.34 Digital filter for Sigma-Delta Modulators (DFSDM) characteristics

Unless otherwise specified, the parameters given in *Table 122* for DFSDM are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DD} supply voltage summarized in *Table 17*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30pF
- Measurement points are done at CMOS levels: 0.5 x VDD

Refer to *Section 5.3.20: I/O port characteristics* for more details on the input/output alternate function characteristics (DFSDM1_CKINx, DFSDM1_DATINx, DFSDM1_CKOUT for DFSDM1).

Table 122. DFSDM measured timing 1.71-3.6V

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{DFSDMCLK}$	DFSDM clock	1.71 < V_{DD} < 3.6 V	-	-	f_{SYSCLK}	MHz
f_{CKIN} ($1/T_{CKIN}$)	Input clock frequency	SPI mode (SITP[1:0]=0,1), External clock mode (SPICKSEL[1:0]=0), 1.71 < V_{DD} < 3.6 V	-	-	20 ($f_{DFSDMCLK}$/4)	
		SPI mode (SITP[1:0]=0,1), External clock mode (SPICKSEL[1:0]=0), 2.7 < V_{DD} < 3.6 V	-	-	20 ($f_{DFSDMCLK}$/4)	
		SPI mode (SITP[1:0]=0,1), Internal clock mode (SPICKSEL[1:0]≠0), 1.71 < V_{DD} < 3.6 V	-	-	20 ($f_{DFSDMCLK}$/4)	
		SPI mode (SITP[1:0]=0,1), Internal clock mode (SPICKSEL[1:0]≠0), 2.7 < V_{DD} < 3.6 V	-	-	20 ($f_{DFSDMCLK}$/4)	
f_{CKOUT}	Output clock frequency	1.71 < V_{DD} < 3.6 V	-	-	20	
$DuCy_{CKOUT}$	Output clock frequency duty cycle	1.71 < V_{DD} < 3.6 V	45	50	55	%

Table 122. DFSDM measured timing 1.71-3.6V (continued)

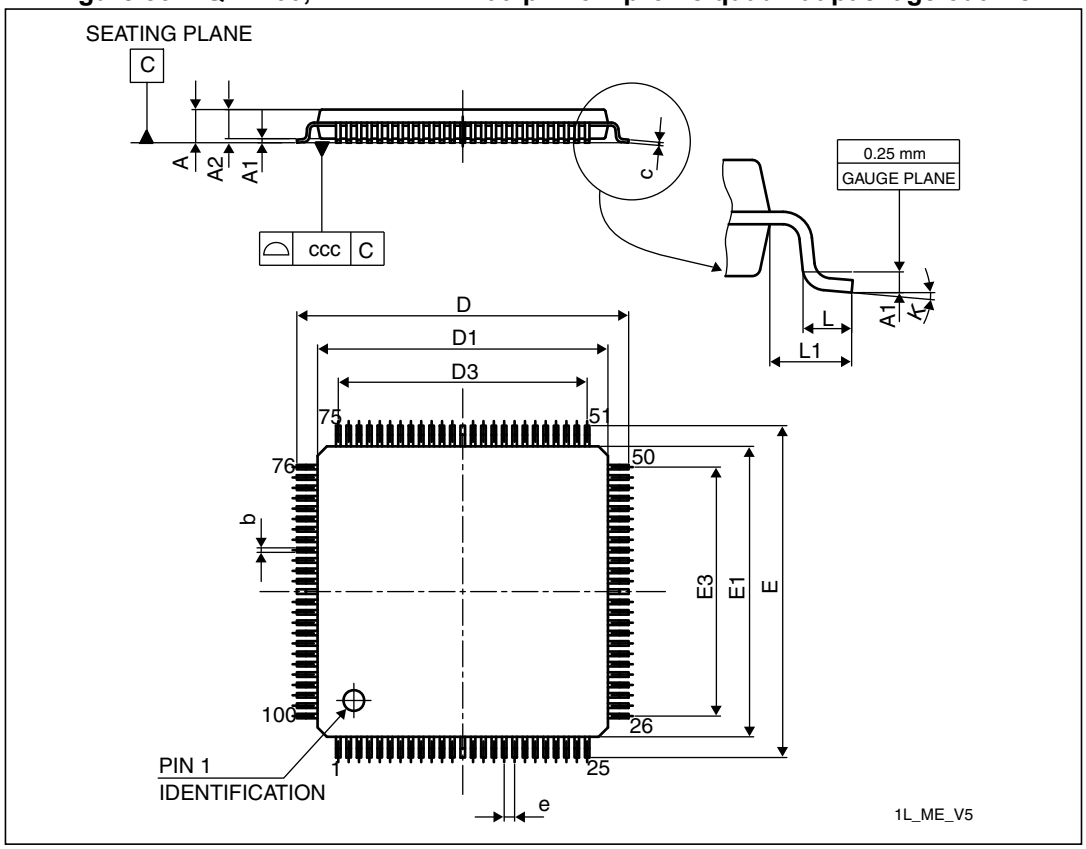
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{wh(CKIN)}$ $t_{wl(CKIN)}$	Input clock high and low time	SPI mode (SITP[1:0]=0,1), External clock mode (SPICKSEL[1:0]=0), 1.71 < V_{DD} < 3.6 V	TCKIN/2 - 0.5	$T_{CKIN}/2$	-	ns
t_{su}	Data input setup time	SPI mode (SITP[1:0]=0,1), External clock mode (SPICKSEL[1:0]=0), 1.71 < V_{DD} < 3.6 V	2	-	-	
t_h	Data input hold time	SPI mode (SITP[1:0]=0,1), External clock mode (SPICKSEL[1:0]=0), 1.71 < V_{DD} < 3.6 V	3	-	-	
$T_{Manchester}$	Manchester data period (recovered clock period)	Manchester mode (SITP[1:0]=2,3), Internal clock mode (SPICKSEL[1:0]≠0), 1.71 < V_{DD} < 3.6 V	(CKOUTDIV+1) * $T_{DFSDMCLK}$	-	(2*CKOUTDIV) * $T_{DFSDMCLK}$	

6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

6.1 LQFP100 14x 14 mm, low-profile quad flat package information

Figure 83. LQFP100, 14 x 14 mm 100-pin low-profile quad flat package outline



1. Drawing is not to scale.

Table 128. LQFP208, 28 x 28 mm, 208-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	--	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	29.800	30.000	30.200	1.1732	1.1811	1.1890
D1	27.800	28.000	28.200	1.0945	1.1024	1.1102
D3	-	25.500	-	-	1.0039	-
E	29.800	30.000	30.200	1.1732	1.1811	1.1890
E1	27.800	28.000	28.200	1.0945	1.1024	1.1102
E3	-	25.500	-	-	1.0039	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7.0°	0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

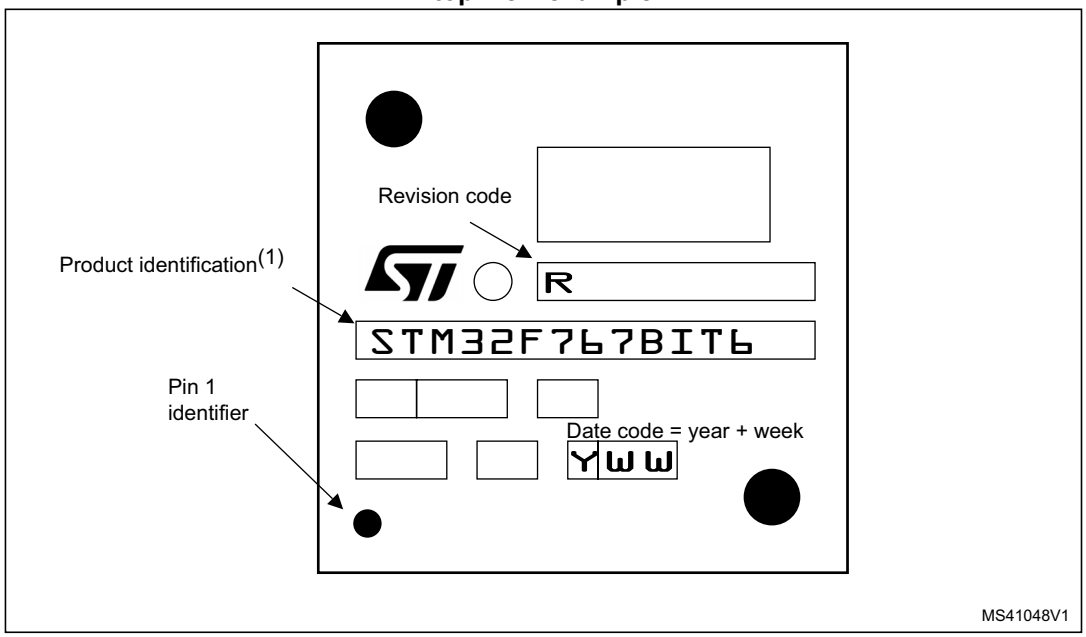
1. Values in inches are converted from mm and rounded to 4 decimal digits.

LQFP208 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

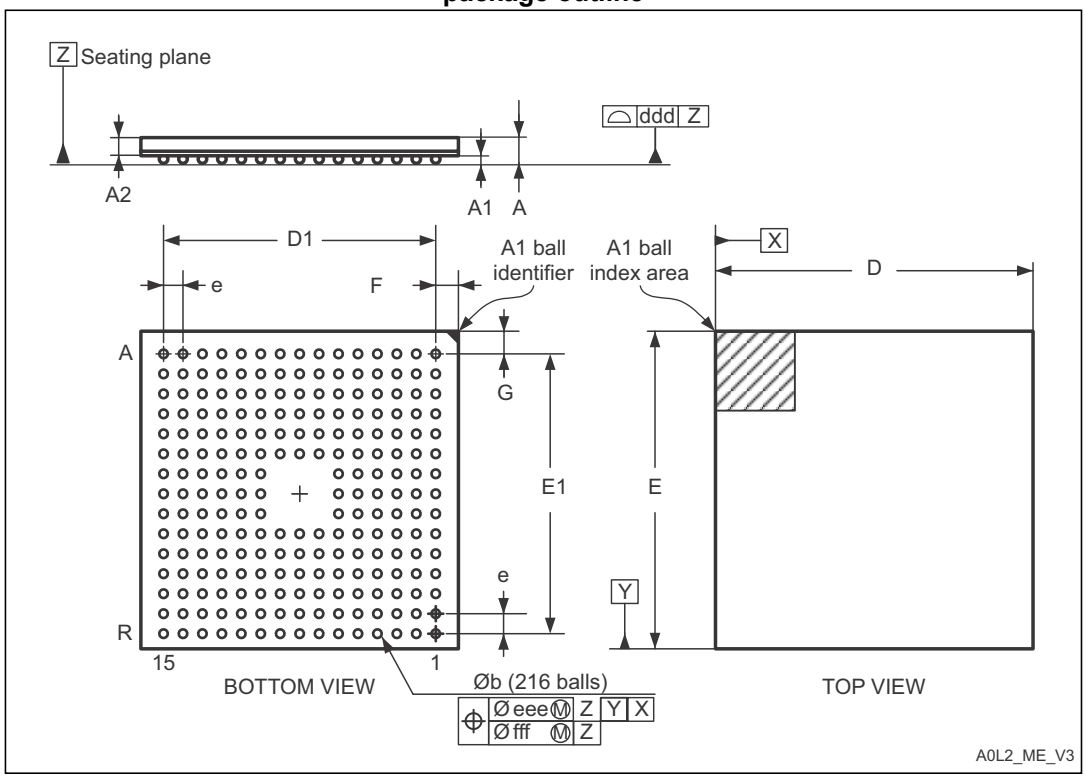
Figure 94. LQFP208, 28 x 28 mm, 208-pin low-profile quad flat package top view example



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

6.7 TFBGA216, 13 x 13 x 0.8 mm thin fine-pitch ball grid array package information

Figure 101. TFBGA216, 13 × 13 × 0.8 mm thin fine-pitch ball grid array package outline



1. Drawing is not to scale.

Table 133. TFBGA216, 13 × 13 × 0.8 mm thin fine-pitch ball grid array package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.100	-	-	0.0433
A1	0.150	-	-	0.0059	-	-
A2	-	0.760	-	-	0.0299	-
b	0.350	0.400	0.450	0.0138	0.0157	0.0177
D	12.850	13.000	13.150	0.5118	0.5118	0.5177
D1	-	11.200	-	-	0.4409	-
E	12.850	13.000	13.150	0.5118	0.5118	0.5177
E1	-	11.200	-	-	0.4409	-
e	-	0.800	-	-	0.0315	-
F	-	0.900	-	-	0.0354	-